

Title (en)  
MEMORY CELL COMPRISING A TRENCH AND METHOD FOR PRODUCTION THEREOF

Title (de)  
SPEICHERZELLE MIT EINEM GRABEN UND VERFAHREN ZU IHRER HERSTELLUNG

Title (fr)  
CELLULE DE MEMOIRE POURVUE D'UNE TRANCHEE ET PROCEDE DE FABRICATION

Publication  
**EP 1366516 A2 20031203 (DE)**

Application  
**EP 02714036 A 20020219**

Priority  
• DE 0200596 W 20020219  
• DE 10111499 A 20010309

Abstract (en)  
[origin: DE10111499C1] Storage cell comprises a substrate (2); a trench (3) having a lower region, a middle region, an upper region and an inner wall arranged in the substrate; an insulation collar (8) arranged in the middle region on the inner wall of the trench; a dielectric layer (9) arranged in the lower region of the trench; a conducting trench filling (10) arranged in the lower region and the middle region of the trench; an epitaxially grown layer (11) arranged in the upper region of the trench on the inner wall; and a barrier layer (60) arranged between the filling and the epitaxially grown layer. An Independent claim is also included for a process for the production of the storage cell. Preferred Features: A second dielectric layer with an inner opening is arranged in the upper region of the trench above the epitaxially grown layer. A second trench is arranged in the epitaxially grown layer.

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**H01L 21/8242**

IPC 8 full level  
**H01L 27/108** (2006.01); **H01L 21/8242** (2006.01)

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